# **14-Stage Binary Ripple Counter With Oscillator** High-Performance Silicon-Gate CMOS

The MC74C4060A is identical in pinout to the standard CMOS MC14060B. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

This device consists of 14 master-slave flip-flops and an oscillator with a frequency that is controlled either by a crystal or by an RC circuit connected externally. The output of each flip-flop feeds the next and the frequency at each output is half of that of the preceding one. The state of the counter advances on the negative-going edge of the Osc In. The active-high Reset is asynchronous and disables the oscillator to allow very low power consumption during stand-by operation.

State changes of the Q outputs do not occur simultaneously because of internal ripple delays. Therefore, decoded output signals are subject to decoding spikes and may have to be gated with Osc Out 2 of the HC4060A.

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2 to 6 V
- Low Input Current: 1 µA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance With JEDEC Standard No. 7A Requirements
- Chip Complexity: 390 FETs or 97.5 Equivalent Gates



# FUNCTION TABLE

Clock	Reset	Output State
	L	No Change
	L	Advance to Next State
Х	Н	All Outputs Are Low



#### **ORDERING INFORMATION**

Device	Package	Shipping
MC74HC4060AN	PDIP-16	2000 / Box
MC74HC4060AD	SOIC-16	48 / Rail
MC74HC4060ADR2	SOIC-16	2500 / Reel
MC74HC4060ADT	TSSOP-16	96 / Rail
MC74HC4060ADTR2	TSSOP-16	2500 / Reel

#### MAXIMUM RATINGS\*

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V <sub>in</sub>	DC Input Voltage (Referenced to GND)	-0.5 to V <sub>CC</sub> + 0.5	V
Vout	DC Output Voltage (Referenced to GND)	-0.5 to V <sub>CC</sub> + 0.5	V
l <sub>in</sub>	DC Input Current, per Pin	± 20	mA
I <sub>out</sub>	DC Output Current, per Pin	± 25	mA
I <sub>CC</sub>	DC Supply Current, $V_{CC}$ and GND Pins	± 50	mA
PD	Power Dissipation in Still Air, Plastic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T <sub>stg</sub>	Storage Temperature Range	– 65 to + 150	°C
ΤL	Lead Temperature, 1 mm from Case for 10 Seconds Plastic DIP, SOIC or TSSOP Package	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq (V_{in} \text{ or } V_{out}) \leq V_{CC}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

\*Maximum Ratings are those values beyond which damage to the device may occur.

Functional operation should be restricted to the Recommended Operating Conditions.

†Derating — Plastic DIP: – 10 mW/°C from 65° to 125°C

SOIC Package: - 7 mW/°C from 65° to 125°C

TSSOP Package: - 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

#### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter			Мах	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)			6.0	V
V <sub>in</sub> , V <sub>out</sub>	DC Input Voltage, Output Voltage (Referenced to GND)			V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature Range, All Package Types			+ 125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise/Fall Time $V_{CC} = 2$ (Figure 1) $V_{CC} = 4$ $V_{CC} = 6$	I.5 V	0 0 0	1000 500 400	ns

\*The oscillator is guaranteed to function at 2.5 V minimum. However, parametrics are tested at 2.0 V by driving Pin 11 with an external clock source.

#### DC CHARACTERISTICS (Voltages Referenced to GND)

				Vcc	Guara	nteed Lin	nit	
Symbol	Parameter	Condition		V	-55 to 25°C	≤85°C	≤125°C	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage	$V_{out} = 0.1V \text{ or } V_{CC} -0.1V$ $ I_{out}  \le 20\mu A$		2.0 3.0 4.5 6.0	1.50 2.10 3.15 4.20	1.50 2.10 3.15 4.20	1.50 2.10 3.15 4.20	V
V <sub>IL</sub>	Maximum Low-Level Input Voltage	$V_{out} = 0.1V \text{ or } V_{CC} - 0.1V$ $ I_{out}  \le 20 \mu A$		2.0 3.0 4.5 6.0	0.50 0.90 1.35 1.80	0.50 0.90 1.35 1.80	0.50 0.90 1.35 1.80	V
V <sub>OH</sub>	Minimum High-Level Output Voltage (Q4-Q10, Q12-Q14)			2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		l <sub>out</sub>	≤ 2.4mA ≤ 4.0mA ≤ 5.2mA	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.20 3.70 5.20	

#### DC CHARACTERISTICS (Voltages Referenced to GND)

					Guara	nteed Lin	nit	
Symbol	Parameter	Condition		V <sub>CC</sub> V	-55 to 25°C	≤85°C	≤125°C	Unit
V <sub>OL</sub>	Maximum Low-Level Output Voltage (Q4-Q10, Q12-Q14)	$\begin{aligned} V_{in} &= V_{IH} \text{ or } V_{IL} \\  I_{out}  &\leq 20 \mu A \end{aligned}$		2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$V_{in} = V_{IH} \text{ or } V_{IL}$	$\begin{split}  I_{out}  &\leq 2.4 \text{mA} \\  I_{out}  &\leq 4.0 \text{mA} \\  I_{out}  &\leq 5.2 \text{mA} \end{split}$	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.40 0.40 0.40	
V <sub>OH</sub>	Minimum High-Level Output Voltage (Osc Out 1, Osc Out 2)	$V_{in} = V_{CC} \text{ or } GND$ $ I_{out}  \le 20 \mu A$		2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		V <sub>in</sub> =V <sub>CC</sub> or GND	$\begin{split}  I_{out}  &\leq 0.7 \text{mA} \\  I_{out}  &\leq 1.0 \text{mA} \\  I_{out}  &\leq 1.3 \text{mA} \end{split}$	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.20 3.70 5.20	
V <sub>OL</sub>	Maximum Low-Level Output Voltage (Osc Out 1, Osc Out 2)	$V_{in} = V_{CC} \text{ or } GND$ $ I_{out}  \le 20 \mu A$		2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		V <sub>in</sub> =V <sub>CC</sub> or GND	$\begin{split}  I_{out}  &\leq 0.7 \text{mA} \\  I_{out}  &\leq 1.0 \text{mA} \\  I_{out}  &\leq 1.3 \text{mA} \end{split}$	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.40 0.40 0.40	
l <sub>in</sub>	Maximum Input Leakage Current	$V_{in} = V_{CC} \text{ or } GND$		6.0	±0.1	±1.0	±1.0	μΑ
ICC	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC} \text{ or } GND$ $I_{out} = 0\mu A$		6.0	4	40	160	μΑ

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

#### **AC CHARACTERISTICS** ( $C_L = 50 \text{ pF}$ , Input $t_r = t_f = 6 \text{ ns}$ )

		v <sub>cc</sub>	Gu			
Symbol	Parameter	V	-55 to 25°C	≤85°C	≤125°C	Unit
f <sub>max</sub>	Maximum Clock Frequency (50% Duty Cycle) (Figures 1 and 4)	2.0 3.0 4.5 6.0	6.0 10 30 50	9.0 14 28 45	8.0 12 25 40	MHz
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Osc In to Q4* (Figures 1 and 4)	2.0 3.0 4.5 6.0	300 180 60 51	375 200 75 64	450 250 90 75	ns
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Osc In to Q14* (Figures 1 and 4)	2.0 3.0 4.5 6.0	500 350 250 200	750 450 275 220	1000 600 300 250	ns
t <sub>PHL</sub>	Maximum Propagation Delay, Reset to Any Q (Figures 2 and 4)	2.0 3.0 4.5 6.0	195 75 39 33	245 100 49 42	300 125 61 53	ns
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Qn to Qn+1 (Figures 3 and 4)	2.0 3.0 4.5 6.0	75 60 15 13	95 75 19 16	125 95 24 20	ns

#### **AC CHARACTERISTICS** ( $C_L = 50 \text{ pF}$ , Input $t_r = t_f = 6 \text{ ns}$ ) - continued

		v <sub>cc</sub>	Guaranteed Limit			
Symbol	Parameter	V	-55 to 25°C	≤85°C	≤125°C	Unit
t <sub>⊤LH</sub> , t <sub>⊤HL</sub>	Maximum Output Transition Time, Any Output (Figures 1 and 4)	2.0 3.0 4.5 6.0	75 27 15 13	95 32 19 16	110 36 22 19	ns
C <sub>in</sub>	Maximum Input Capacitance	•	10	10	10	pF

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High- Speed CMOS Data Book (DL129/D).

\* For  $T_A = 25^{\circ}C$  and  $C_L = 50$  pF, typical propagation delay from Clock to other Q outputs may be calculated with the following equations:

 $V_{CC} = 2.0 \text{ V: } t_P = [93.7 + 59.3 (n-1)] \text{ ns}$  $V_{CC} = 3.0 \text{ V: } t_P = [61.5+ 34.4 (n-1)] \text{ ns}$   $V_{CC} = 4.5$  V:  $t_P = [30.25 + 14.6 (n-1)]$  ns  $V_{CC} = 6.0$  V:  $t_P = [24.4 + 12 (n-1)]$  ns

		Typical @ 25°C, V <sub>CC</sub> = 5.0 V	
C <sub>PD</sub>	Power Dissipation Capacitance (Per Package)*	35	pF

\* Used to determine the no- load dynamic power consumption: P<sub>D</sub> = C<sub>PD</sub> V<sub>CC</sub><sup>2</sup>f + I<sub>CC</sub> V<sub>CC</sub>. For load considerations, see Chapter 2 of the ON Semiconductor High- Speed CMOS Data Book (DL129/D).

#### **TIMING REQUIREMENTS** (Input $t_r = t_f = 6 \text{ ns}$ )

		Vcc	V <sub>CC</sub> Guaranteed Limit			
Symbol	Parameter	V	-55 to 25°C	≤85°C	≤125°C	Unit
t <sub>rec</sub>	Minimum Recovery Time, Reset Inactive to Clock (Figure 2)	2.0 3.0 4.5 6.0	100 75 20 17	125 100 25 21	150 120 30 25	ns
t <sub>w</sub>	Minimum Pulse Width, Clock (Figure 1)	2.0 3.0 4.5 6.0	75 27 15 13	95 32 19 16	110 36 23 19	ns
t <sub>w</sub>	Minimum Pulse Width, Reset (Figure 2)	2.0 3.0 4.5 6.0	75 27 15 13	95 32 19 16	110 36 23 19	ns
t <sub>r</sub> , t <sub>f</sub>	Maximum Input Rise and Fall Times (Figure 1)	2.0 3.0 4.5 6.0	1000 800 500 400	1000 800 500 400	1000 800 500 400	ns

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

### **PIN DESCRIPTIONS**

#### INPUTS

#### Osc In (Pin 11)

Negative-edge triggering clock input. A high-to-low transition on this input advances the state of the counter. Osc In may be driven by an external clock source.

#### Reset (Pin 12)

Active-high reset. A high level applied to this input asynchronously resets the counter to its zero state (forcing all Q outputs low) and disables the oscillator.

#### OUTPUTS

#### Q4—Q10, Q12-Q14 (Pins 7, 5, 4, 6, 13, 15, 1, 2, 3)

Active-high outputs. Each Qn output divides the Clock input frequency by  $2^{N}$ . The user should note the Q1, Q2, Q3 and Q11 are not available as outputs.

#### Osc Out 1, Osc Out 2 (Pins 9, 10)

Oscillator outputs. These pins are used in conjunction with Osc In and the external components to form an oscillator. When Osc In is being driven with an external clock source, Osc Out 1 and Osc Out 2 must be left open circuited. With the crystal oscillator configuration in Figure 6, Osc Out 2 must be left open circuited.

#### SWITCHING WAVEFORMS











Figure 3.



\*Includes all probe and jig capacitance

#### Figure 4. Test Circuit









Figure 7. Pierce Crystal Oscillator Circuit

TABLE 1. CRYSTAL OSCILLATOR AMPLIFIER SPECIFICATIONS (T <sub>A</sub> = 25	$5^{\circ}$ C; Input = Pin 11, Output = Pin 10)
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Туре		Positive Reactance (Pierce)
Input Resistance, R <sub>in</sub>		60MΩ Minimum
Output Impedance, Z <sub>out</sub> (4.5V Supply)		200Ω (See Text)
Input Capacitance, C <sub>in</sub>		5pF Typical
Output Capacitance, C <sub>out</sub>		7pF Typical
Series Capacitance, C <sub>a</sub>		5pF Typical
Open Loop Voltage Gain with Output at Full Swing, $\alpha$	3Vdc Supply 4Vdc Supply 5Vdc Supply 6Vdc Supply	5.0 Expected Minimum 4.0 Expected Minimum 3.3 Expected Minimum 3.1 Expected Minimum

### PIERCE CRYSTAL OSCILLATOR DESIGN



Value are supplied by crystal manufacturer (parallel resonant crystal).

#### Figure 8. Equivalent Crystal Networks



NOTE: C = C1 + C<sub>in</sub> and R = R1 + R<sub>out</sub>. C<sub>o</sub> is considered as part of the load. C<sub>a</sub> and R<sub>f</sub> typically have minimal effect below 2MHz.





Values are listed in Table 1.

Figure 10. Parasitic Capacitances of the Amplifier

#### **DESIGN PROCEDURES**

The following procedure applies for oscillators operating below 2MHz where Z is a resistor R1. Above 2MHz, additional impedance elements should be considered:  $C_{out}$  and  $C_a$  of the amp, feedback resistor  $R_f$ , and amplifier phase shift error from 180°C.

Step 1: Calculate the equivalent series circuit of the crystal at the frequency of oscillation.

$$Z_{e} = \frac{-jX_{C_{0}}(R_{s} + jX_{L_{s}} - jX_{C_{s}})}{-jX_{C_{0}} + R_{s} + jX_{L_{s}} - jX_{C_{s}}} = R_{e} + jX_{e}$$

Reactance  $jX_e$  should be positive, indicating that the crystal is operating as an inductive reactance at the oscillation frequency. The maximum  $R_s$  for the crystal should be used in the equation.

Step 2: Determine  $\beta$ , the attenuation, of the feedback network. For a closed-loop gain of 2,  $A_{\nu}\beta = 2, \beta = 2/A_{\nu}$  where  $A_{\nu}$  is the gain of the HC4060A amplifier.

Step 3: Determine the manufacturer's loading capacitance. For example: A manufacturer may specify an external load capacitance of 32pF at the required frequency.

Step 4: Determine the required Q of the system, and calculate  $R_{load}$ , For example, a manufacturer specifies a crystal Q of 100,000. In-circuit Q is arbitrarily set at 20% below crystal Q or 80,000. Then  $R_{load} = (2\pi f_o L_S/Q) - R_s$  where  $L_s$  and  $R_s$  are crystal parameters.

Step 5: Simultaneously solve, using a computer,

$$\beta = \frac{X_{C} \cdot X_{C2}}{R \cdot R_{e} + X_{C2} (X_{e} - X_{C})} \quad \text{(with feedback phase shift = 180°)}$$
(Eq 1)

$$X_{e} = X_{C2} + X_{C} + \frac{R_{e}X_{C2}}{R} = X_{Cload}$$
 (where the loading capacitor is an external load, not including C<sub>o</sub>) (Eq 2)

$$R_{\text{load}} = \frac{R_{X_{C_0}X_{C_2}}[(X_C + X_{C_2})(X_C + X_{C_0}) - X_C(X_C + X_{C_0} + X_{C_2})]}{X_{C_2}^2(X_C + X_{C_0})^2 + R_C^2(X_C + X_{C_0} + X_{C_2})^2}$$
(Eq 3)

Here  $R = R_{out} + R1$ .  $R_{out}$  is amp output resistance, R1 is Z. The C corresponding to  $X_C$  is given by  $C = C1 + C_{in}$ .

Alternately, pick a value for R1 (i.e, let  $R1 = R_S$ ). Solve Equations 1 and 2 for C1 and C2. Use Equation 3 and the fact that  $Q = 2\pi f_0 L_s/(R_s + R_{load})$  to find in-circuit Q. If Q is not satisfactory pick another value for R1 and repeat the procedure.

#### **CHOOSING R1**

Power is dissipated in the effective series resistance of the crystal. The drive level specified by the crystal manufacturer is the maximum stress that a crystal can withstand without damage or excessive shift in frequency. R1 limits the drive level.

To verify that the maximum dc supply voltage does not overdrive the crystal, monitor the output frequency as a function of voltage at Osc Out 2 (Pin 9). The frequency should increase very slightly as the dc supply voltage is increased. An overdriven crystal will decrease in frequency or become unstable with an increase in supply voltage. The operating supply voltage must be reduced or R1 must be increased in value if the overdriven condition exists. The user should note that the oscillator start-up time is proportional to the value of R1.

#### SELECTING R<sub>f</sub>

The feedback resistor,  $R_f$ , typically ranges up to 20M $\Omega$ .  $R_f$  determines the gain and bandwidth of the amplifier. Proper bandwidth insures oscillation at the correct frequency plus roll-off to minimize gain at undesirable frequencies, such as

the first overtone.  $R_f$  must be large enough so as to not affect the phase of the feedback network in an appreciable manner.

#### ACKNOWLEDGEMENTS AND RECOMMENDED REFERENCES

The following publications were used in preparing this data sheet and are hereby acknowledged and recommended for reading:

Technical Note TN-24, Statek Corp.

Technical Note TN-7, Statek Corp.

D. Babin, "Designing Crystal Oscillators", Machine Design, March 7, 1985.

D. Babin, "Guidelines for Crystal Oscillator Design", Machine Design, April 25, 1985.

#### ALSO RECOMMENDED FOR READING:

E. Hafner, "The Piezoelectric Crystal Unit-Definitions and Method of Measurement", Proc. IEEE, Vol. 57, No. 2, Feb., 1969.

D. Kemper, L. Rosine, "Quartz Crystals for Frequency Control", Electro-Technology, June, 1969.

P. J. Ottowitz, "A Guide to Crystal Selection", Electronic Design, May, 1966.



Figure 11. Timing Diagram

#### PACKAGE DIMENSIONS

PDIP-16 **N SUFFIX** CASE 648-08 ISSUE R



NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI

- DIMENSIONING AND TOLENANCING FER AINSI Y14.5M, 1982.
  CONTROLLING DIMENSION: INCH.
  DIMENSION LTO CENTER OF LEADS WHEN FORMED PARALLEL.
  DIMENSION B DOES NOT INCLUDE MOLD FLASH.
  ROUNDED CORNERS OPTIONAL.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.740	0.770	18.80	19.55
В	0.250	0.270	6.35	6.85
С	0.145	0.175	3.69	4.44
D	0.015	0.021	0.39	0.53
F	0.040	0.070	1.02	1.77
G	0.	100 BSC	2	.54 BSC
H	0.	050 BSC	1	.27 BSC
J	0.008	0.015	0.21	0.38
K	0.110	0.130	2.80	3.30
L	0.295	0.305	7.50	7.74
М	0°	10°	0°	10°
S	0.020	0.040	0.51	1.01

SOIC-16 **D SUFFIX** CASE 751B-05 **ISSUE J** 



NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI
- 2. 3.
- 4.
- DIMENSIONING AND TOLERANCING PER ANS Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION ALLOWABLE DAMBAR PROTRUSION ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION 5. MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
М	<b>0</b> °	<b>7</b> °	0°	<b>7</b> °
Р	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

#### PACKAGE DIMENSIONS



NOT	ES:		

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR 3. GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- 4.
- SIDE. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. 5. 6.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
Κ	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
М	0 °	8°	0 °	8 °

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